

N-Channel Logic Level Enhancement Mode Field Effect Transistor



SOT-23, 3 Lead, 1.25X2
CASE 419AB

BSS138W

Description

These N-Channel Enhancement Mode Field Effect Transistor. These products have been Designed to minimize on-state resistance while provide rugged, reliable, and fast switching performance.

These products are particularly suited for low voltage, low current applications such as small servo motor control, power MOSFET gate drivers, and other switching applications.

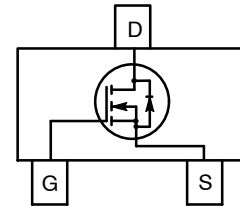
Features

- $R_{DS(on)} = 3.5 \Omega @ V_{GS} = 10 V, I_D = 0.22 A$
 $R_{DS(on)} = 6.0 \Omega @ V_{GS} = 4.5 V, I_D = 0.22 A$
- High Density Cell Design For Extremely Low $R_{DS(on)}$
- Rugged and Reliable
- Compact Industry Standard SOT-323 Surface Mount Package
- These Devices are Pb-Free and Halide Free

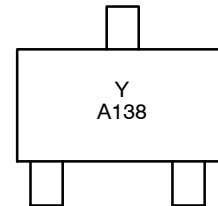
ABSOLUTE MAXIMUM RATINGS $T_A = 25^\circ C$ unless otherwise noted

Symbol	Parameter	Value	Unit
V_{DSS}	Drain to Source Voltage	50	V
V_{GSS}	Gate to Source Voltage	± 20	V
I_D	Drain Current – Continuous (Note 1) – Pulsed	0.21 0.84	A A
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ C$
T_L	Maximum Lead Temperature for Soldering Purposes, 1/16" from Case for 10 Seconds	300	$^\circ C$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



MARKING DIAGRAM



Y = Year
A = Assembly Plant Code
138 = Specific Device Code

ORDERING INFORMATION

Device	Package	Shipping†
BSS138W	SOT-323 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, [BRD8011/D](#).

BSS138W

THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
P _D	Maximum Power Dissipation Derate Above 25°C (Note 1)	340	mW
		2.72	mW/°C
R _{θJA}	Thermal Resistance, Junction to Ambient (Note 1)	367	°C/W

ELECTRICAL CHARACTERISTICS T_A = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
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Off Characteristics

BV _{DSS}	Drain to Source Breakdown Voltage	V _{GS} = 0 V, I _D = 250 μA	50	–	–	V
$\frac{\Delta BV_{DSS(th)}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C	–	71	–	mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 50 V, V _{GS} = 0 V V _{DS} = 50 V, V _{GS} = 0 V, T _J = 125°C V _{DS} = 30 V, V _{GS} = 0 V	–	–	0.5 5 100	μA μA nA
I _{GSS}	Gate–Body Leakage	V _{GS} = ±20 V, V _{DS} = 0 V	–	–	±100	nA

On Characteristics (Note2)

V _{GS(th)}	Gate to Threshold Voltage	V _{DS} = V _{GS} , I _D = 1 mA	0.8	1.3	1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Threshold Voltage Temperature Coefficient	I _D = 1 mA, Referenced to 25°C	–	–3.9	–	mV/°C
R _{DS(on)}	Static Drain–Source On–Resistance	V _{GS} = 10 V, I _D = 0.22 A V _{GS} = 4.5 V, I _D = 0.22 A V _{GS} = 10 V, I _D = 0.22 A, T _J = 125°C	–	1.17 1.36 2.16	3.5 6.0 5.8	Ω Ω Ω
I _{D(on)}	On–State Drain Current	V _{GS} = 10 V, V _{DS} = 5 V	0.2	–	–	A
g _{FS}	Forward Transconductance	V _{DS} = 10 V, I _D = 0.22 A	0.12	–	–	S

Dynamic Characteristics

C _{ISS}	Input Capacitance	V _{DS} = 25 V, V _{GS} = 0 V, f = 1.0 MHz	–	38	–	pF
C _{OSS}	Output Capacitance		–	5.9	–	pF
C _{RSS}	Reverse Transfer Capacitance		–	3.5	–	pF
R _g	Gate Resistance	V _{GS} = 15 mV, f = 1.0 MHz	–	11	–	Ω

Switching Characteristics

t _{d(on)}	Turn–On Delay Time	V _{DD} = 30 V, I _D = 0.29 A, V _{GS} = 10 V, R _{GEN} = 6 Ω	–	2.3	5	ns
t _r	Turn–On Rise Time		–	1.9	18	ns
t _{d(off)}	Turn–Off Delay Time		–	6.7	36	ns
t _f	Turn–Off Fall Time		–	6.5	14	ns
Q _g	Total Gate Change	V _{DS} = 25 V, I _D = 0.22 A, V _{GS} = 10 V	–	1.1	–	nC
Q _{gs}	Gate–Source Change		–	0.12	–	nC
Q _{gd}	Gate–Drain Change		–	0.22	–	nC

Drain–Source Diode Characteristics

I _S	Maximum Continuous Drain–Source Diode Forward Current	–	–	0.22	A	
V _{SD}	Drain–Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 0.44 A (Note 2)	–	–	1.4	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- 367°C/W When Mounted on a minimum pad.
- Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%

TYPICAL CHARACTERISTICS

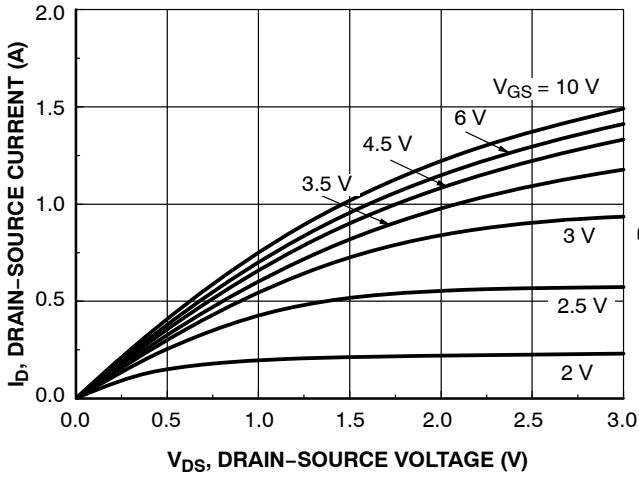


Figure 1. On-Region Characteristics

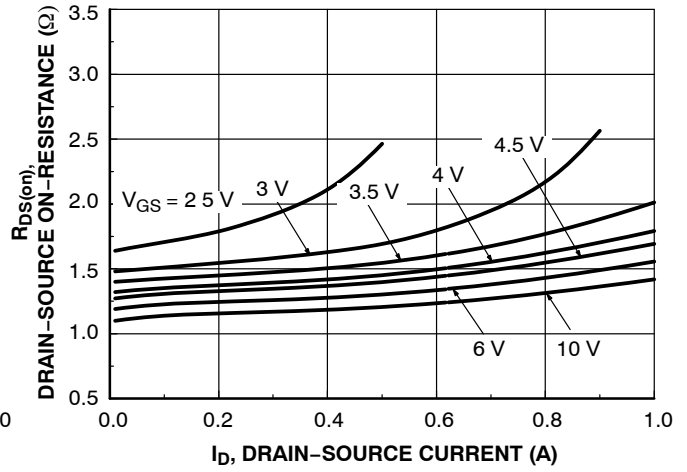


Figure 2. On-Resistance Variation With Drain Current and Gate Voltage

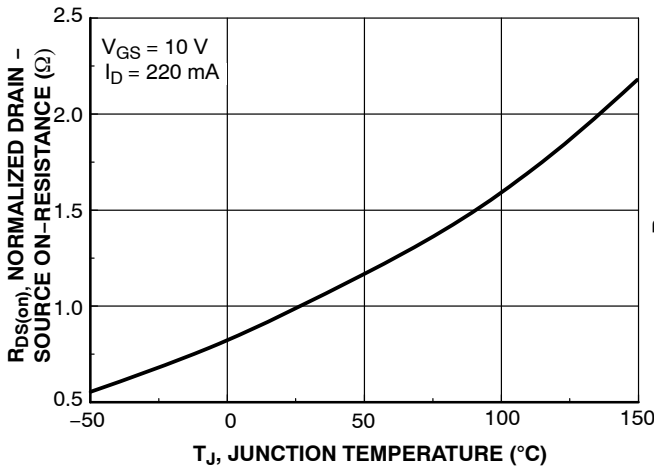


Figure 3. On-Resistance Variation with Temperature.

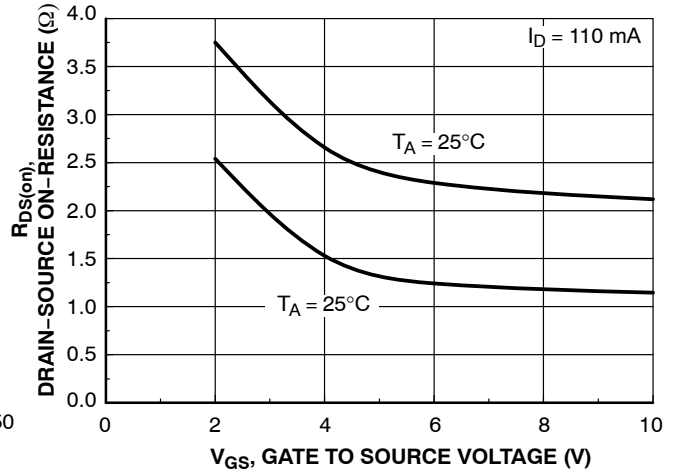


Figure 4. On-Resistance Variation with Gate-to-Source Voltage

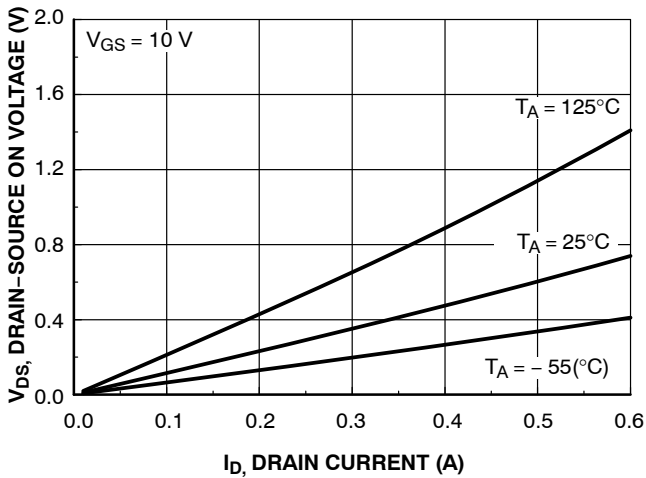


Figure 5. Drain-Source On Voltage with Temperature.

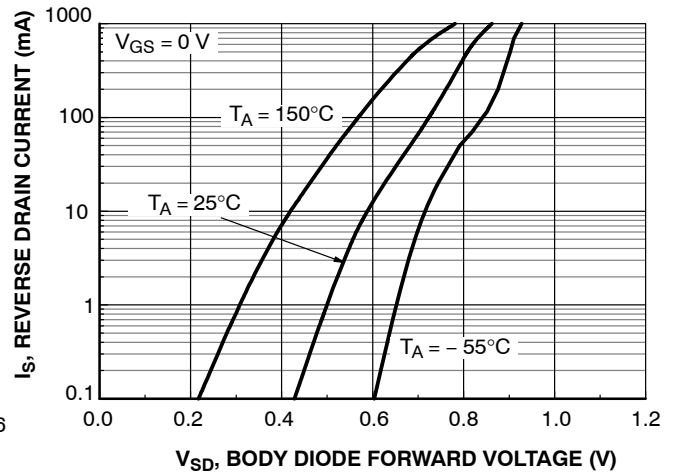


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature

TYPICAL CHARACTERISTICS (continued)

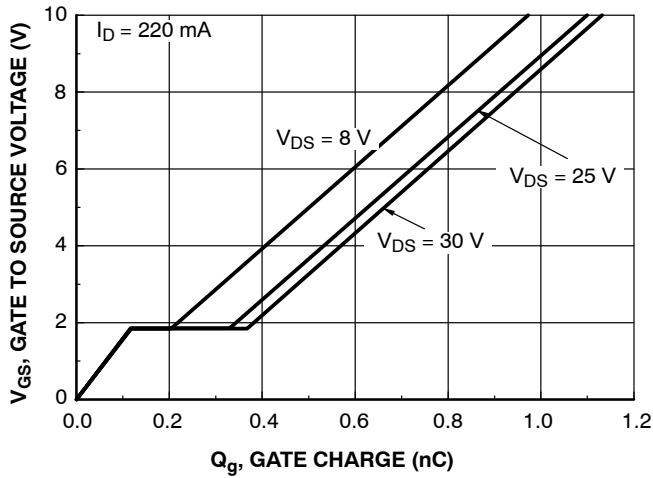


Figure 7. Gate Charge Characteristics

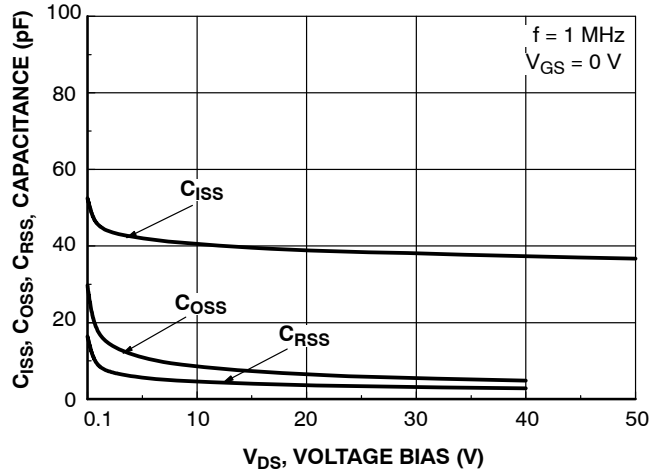


Figure 8. Capacitance Characteristics

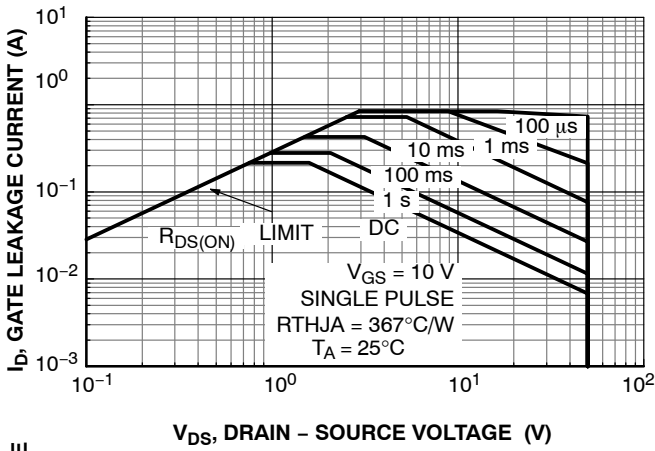


Figure 9. Maximum Safe Operating Area

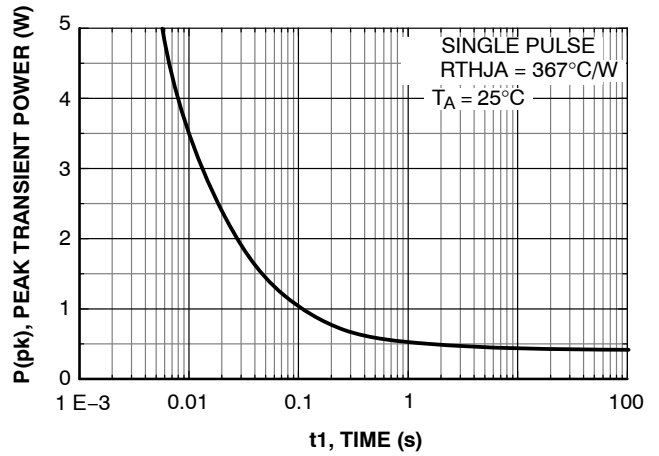


Figure 10. Single Pulse Maximum Power Dissipation

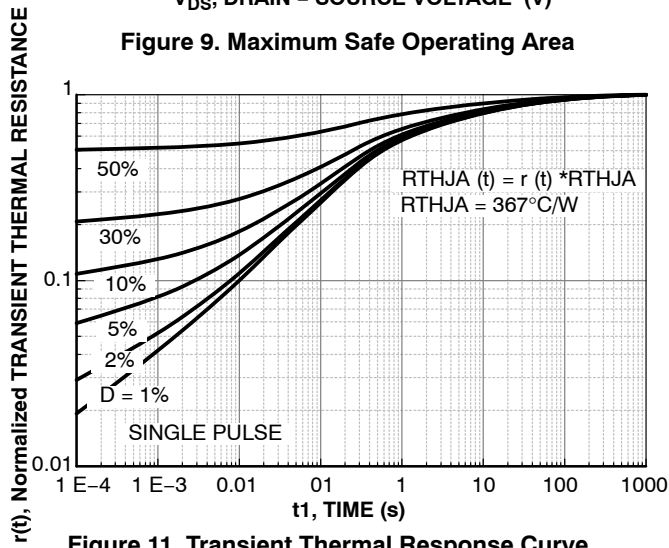


Figure 11. Transient Thermal Response Curve

MECHANICAL CASE OUTLINE

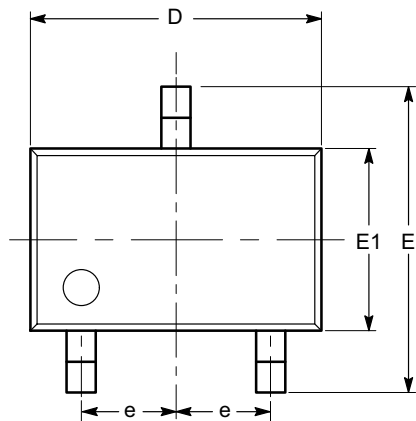
PACKAGE DIMENSIONS

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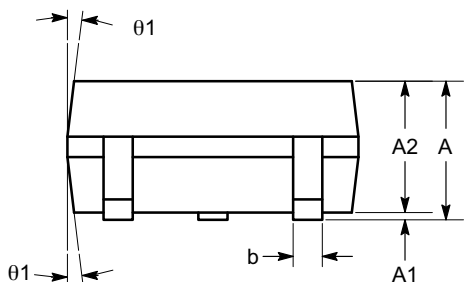
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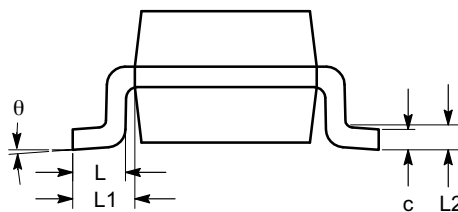


TOP VIEW

SYMBOL	MIN	NOM	MAX
A	0.80		1.10
A1	0.00		0.10
A2	0.80	0.90	1.00
b	0.15		0.30
c	0.08		0.22
D	1.80	2.00	2.20
E	1.80	2.10	2.40
E1	1.15	1.25	1.35
e	0.65 BSC		
L	0.26	0.36	0.46
L1	0.42 REF		
L2	0.15 BSC		
θ	0°		8°
$\theta 1$	4°		10°



SIDE VIEW



END VIEW

Notes:

- (1) All dimensions are in millimeters. Angles in degrees.
- (2) Complies with JEDEC MO-203.

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